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B1 potential), sudden variations in the potential thereof can be absorbed. Also, the potential of the semiconductor chip 20 itself is stabilized.

IN THE CLAIMS:

Please cancel claims 11 and 20 without prejudice to or disclaimer of the subject matter contained therein.

Please replace claims 1 and 12 as follows:

1. (Amended) A method of manufacture of a semiconductor device, comprising the steps of:

providing an adhesive between a surface of a semiconductor chip having a plurality of electrodes on which said electrodes are provided and a surface of a substrate having a plurality of leads formed on which said leads are formed;

positioning at least one of said plurality of electrodes to oppose at least one of said plurality of leads; and

applying pressure in a direction such as to make a gap between said semiconductor chip and said substrate narrower;

wherein on the surface of said substrate on which said leads are formed, in a region being at least part of a region of adherence of said semiconductor chip, a film is formed with a lower adhesion to said adhesive than a base material of said substrate, the film formed in such a shape as to avoid the electrodes.

12. (Amended) A semiconductor device comprising:

a semiconductor chip having a plurality of electrodes;

a substrate on which is formed a plurality of leads; and

an adhesive provided between a surface of said semiconductor chip on which said electrodes are formed and a surface of said substrate on which said leads are formed, and adhering said semiconductor chip and said substrate,